



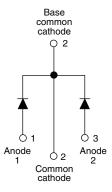
www.vishay.com

Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 2 x 8 A



TO-247AC



PRODUCT SUMMARY	
Package	TO-247AC
I _{F(AV)}	2 x 8 A
V _R	1200 V
V _F at I _F	2.4 V
t _{rr} typ.	28 ns
T _J max.	150 °C
Diode variation	Single die

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC®-JESD47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS
COMPLIANT
HALOGEN
FREE
Available

BENEFITS

- · Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA16PA120C... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A per leg continuous current, the VS-HFA16PA120C... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16PA120C... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _R		1200	V					
Maximum continuous forward current per leg	1	T _C = 100 °C	8						
per device	I _F		16	Α					
Single pulse forward current	I _{FSM}		130	A					
Maximum repetitive forward current	I _{FRM}		32						
Maximum navvey discipation	0	T _C = 25 °C	73.5	W					
Maximum power dissipation	P_{D}	T _C = 100 °C	29	VV					
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C					



VS-HFA16PA120CPbF, VS-HFA16PA120C-N3

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ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ	1200	-	-					
Maximum forward voltage		I _F = 8.0 A	-	2.6	3.3	V				
	V_{FM}	I _F = 16 A	-	3.4	4.3					
		I _F = 8.0 A, T _J = 125 °C	-	2.4	3.1					
Maximum reverse		V _R = V _R rated	-	0.31	10					
leakage current	I _{RM}	T _J = 125 °C, V _R = 0.8 x V _R rated	-	135	1000	μA				
Junction capacitance	C _T	V _R = 200 V	-	11	20	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package	-	8.0	-	nH				

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		28	-				
	t _{rr1}	T _J = 25 °C		-	63	95	ns			
	t _{rr2}	T _J = 125 °C		-	106	160				
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.5	8.0	- A - nC - A/μs			
	I _{RRM2}	T _J = 125 °C	I _F = 8.0 A dI _F /dt = 200 A/µs	-	6.2	11				
Povorco rocovory chargo	Q _{rr1}	T _J = 25 °C	$V_{\rm R} = 200 \text{ V}$	-	140	380				
Reverse recovery charge	Q _{rr2}	T _J = 125 °C	11	-	335	880				
Peak rate of recovery current during t _b	dI _{(rec)M} /dt1	T _J = 25 °C		-	133	-				
	dI _{(rec)M} /dt2	T _J = 125 °C		-	85	-				

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	1.7					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.25	-					
Weight			-	6.0	-	g				
vveignt			-	0.21	-	OZ.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-247AC (JEDEC)	HFA16PA120C			•				

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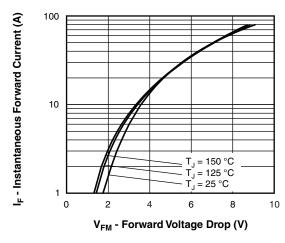


Fig. 1 - Maximum Forward Voltage Drop Characteristics

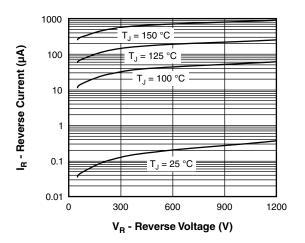


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

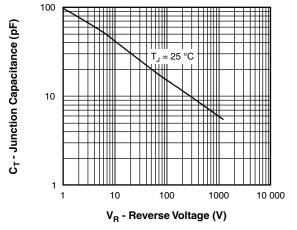


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

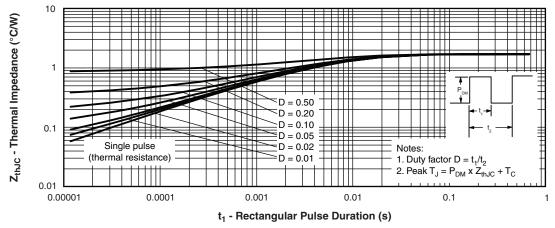


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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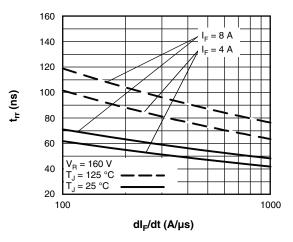


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

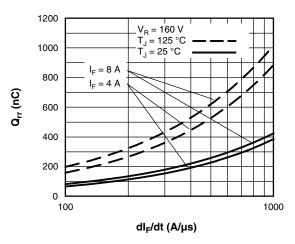


Fig. 7 - Typical Stored Charge vs. dl_F/dt

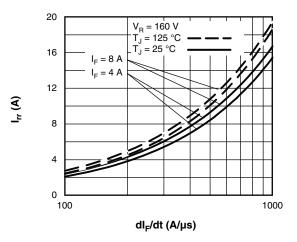


Fig. 6 - Typical Recovery Current vs. dl_F/dt

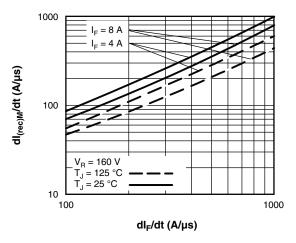


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

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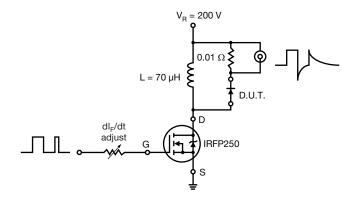
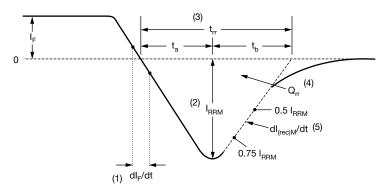


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RBM} and 0.50 I_{RBM} extrapolated to zero current.
- (4) ${\rm Q_{rr}}$ area under curve defined by ${\rm t_{rr}}$ and ${\rm I_{RRM}}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

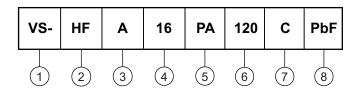
Fig. 10 - Reverse Recovery Waveform and Definitions

VS-HFA16PA120CPbF, VS-HFA16PA120C-N3

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

- Electron irradiated

Current rating (16 = 16 A)

5 - PA = TO-247AC

6 - Voltage rating: (120 = 1200 V)

7 - Circuit configuration

C = Common cathode

7 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION								
VS-HFA16PA120CPbF	25	500	Antistatic plastic tube						
VS-HFA16PA120C-N3	25	500	Antistatic plastic tube						

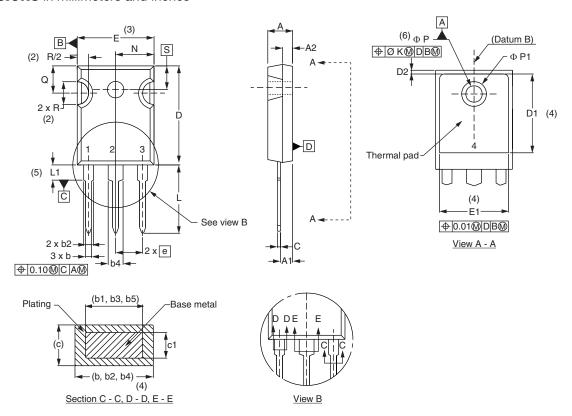
LINKS TO RELATED DOCUMENTS							
Dimensions <u>www.vishay.com/doc?95542</u>							
Part marking information	TO-247ACPbF	www.vishay.com/doc?95226					
	TO-247AC-N3	www.vishay.com/doc?95007					



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TO-247 - 50 mils L/F

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.65	5.31	0.183	0.209			D2	0.51	1.35	0.020	0.053	
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3
A2	1.17	1.37	0.046	0.054			E1	13.46	-	0.53	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			ØΚ	0.2	254	0.0)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			Ν	7.62	BSC	0.3		
b5	2.59	3.38	0.102	0.133			ØΡ	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035			Ø P1	-	7.39	-	0.291	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	'BSC	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- $^{(7)}$ Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



Legal Disclaimer Notice

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